



NATIONAL INSTITUTE OF TECHNOLOGY, TIRUCHIRAPPALLI

DEPARTMENT OF ELECTRICAL & ELECTRONICS ENGINEERING

COURSE PLAN – PART I			
Name of the programme and specialization	B.Tech. – Electrical and Electronics Engineering		
Course Title	Electron Devices		
Course Code	EEPC13	No. of Credits	03
Course Code of Pre-requisite subject(s)	Basic Physics		
Session	August 2022	Section (if, applicable)	A
Name of Faculty	Dr. Shelas Sathyan	Department	EEE
Official Email	Shelassathyan@nitt.edu	Telephone No.	9561450634
Name of Course Coordinator(s) (if, applicable)	NA		
Official E-mail	NA	Telephone No.	NA
Course Type (please tick appropriately)	<input checked="" type="checkbox"/> Core course	<input type="checkbox"/> Elective course	
Syllabus (approved in BoS)			
<ul style="list-style-type: none"> Semi-conductors – charge carriers, electrons and holes in intrinsic and extrinsic semi-conductors –Hall effect. Diodes – PN junction – current equation – Junction Capacitance – breakdown characteristics of Zener diode, Tunnel diode, Schottky diode. Bipolar junction transistors – Characteristics – Analysis of CB, CE, CC amplifier configurations. Unipolar devices – FET, MOSFET, UJT and Opto-Electronic devices – theory and characteristics. Rectifiers and switched mode power supplies – theory and design, filter circuits, applications. 			
Textbooks:			
<ol style="list-style-type: none"> David, A. Be Electronic Devices and Circu PHI, 5th Edition, 2008 Millman and Halk Electronic Devices and Circu cGraw - Hill International Student, 2nd Edition, 2007. Albert Malvino and David J Bates, Electronic Principal McGraw Hill, 7th Edition, 2007 			
COURSE OBJECTIVES			
To educate on the construction and working of common electronic devices and to prepare for application areas.			
MAPPING OF COs with POs			
Course Outcomes: Upon completion of the course, the student will be able to		Programme Outcomes (PO)	
1. Understand the semiconductor physics of the intrinsic, p and n materials and various devices and characteristics.		2,3,8,9	



2. Analyze simple diode circuits under DC and AC excitation.	1,2,8,9
3. Analyze and design simple amplifier circuits using BJT in CE, CC and CB configurations.	1,2,8,9
4. Understand the analysis and salient features of CE, CC & CB amplifier circuits.	1,2,3,8,9
5. Understand the construction and characteristics of FET, MOSFET and UJT.	1,2,3,8,9

COURSE PLAN – PART II

COURSE OVERVIEW

The basic understanding of electronics devices is established by studying the semiconductor material like p-type and n-type material. After knowing the material, PN junction semiconductor devices will be discussed which is necessary to understand the construction of devices like diode, BJT, FET. Operation of these devices along with its input and output characteristics will be discussed. After understanding the devices, some of its applications like rectifiers, switched mode power supplies, filter circuit etc. will be discussed.

COURSE TEACHING AND LEARNING ACTIVITIES

S.No.	Week/Contact Hours	Topic	Mode of Delivery
1	August 2 nd week to 4 th week	Introduction to the course, semiconductor Charge carrier, intrinsic and extrinsic semiconductor Transportation of carrier: Drift and diffusion, Hall effect	Chalk and Talk
2	September 1 st week to 4 th week	PN Junction, Current equation diode, characteristics, small signal model of diode, junction capacitance Zener diode: break down characteristics, tunnel diode, Schottky diode Application of diode	



3	October 1 st week to 4 th week	Introduction to BJT, types of BJT. its operation and characteristics BJT: Analysis of CB, CE, CC amplifier configuration	Chalk and Talk
4	November 1 st week 3 rd week	Introduction to FET, MOSFET, construction Operation of MOSFET and its characteristics Operation of MOSFET and its characteristics	
5	4 th week of September and 1 st week of December	Switched mode power supplies, theory, and design Filter circuits	

Course Assessment Methods

S.No.	Mode of Assessment	Week/Date	Duration	% Weightage
1	Class Test-1	3 rd week of September	1Hr	20
2	Class Test-2	3 rd week of October	1 Hr	20
3	Assignment	Through Out the Semester	-	10
4	Final Examination	December 2 nd Week	3Hr	50
(CPA)	Compensation Assessment*		1 Hr	20

***mandatory; refer to guidelines on page 4**



COURSE EXIT SURVEY (mention the ways in which the feedback about the course shall be assessed)

- Feedback from students during class committee meetings
- Feedback through questionnaire

COURSE POLICY (including compensation assessment to be specified)

- The above course has 5 assessments in total and one compensation (A1, A2, A3, A4, CPA)
- There will be no compensation assessment for Assessment-3
- The compensation assessment will include the complete syllabus

ATTENDANCE POLICY (A uniform attendance policy as specified below shall be followed)

- At least 75% attendance in each course is mandatory.
- A maximum of 10% shall be allowed under On Duty (OD) category.
- Students with less than 65% of attendance shall be prevented from writing the final assessment and shall be awarded 'V' grade.

ACADEMIC DISHONESTY & PLAGIARISM

- Possessing a mobile phone, carrying bits of paper, talking to other students, copying from others during an assessment will be treated as punishable dishonesty.
- Zero mark to be awarded for the offenders. For copying from another student, both students get the same penalty of zero mark.
- The departmental disciplinary committee including the course faculty member, PAC chairperson and the HoD, as members shall verify the facts of the malpractice and award the punishment if the student is found guilty. The report shall be submitted to the Academic office.
- The above policy against academic dishonesty shall be applicable for all the programmes.

ADDITIONAL INFORMATION, IF ANY

- The faculty is available for consultation at times as per the information given by the faculty.
- Queries and feedback may also be emailed to the faculty directly: email: shelassathyan@nitt.edu

FOR APPROVAL

Course Faculty

CC- Chairperson

HOD